Silicon N-MOSFET Transistor

BUK444-500B

500V / 1.9A

DATASHEET

OEM – Philips

Source: Philips Databook MOSFET 1989

Datasheet Rev. 1.0 – 10/20 – data without warranty / liability

PowerMOS transistor

BUK444-500A
BUK444-500B

GENERAL DESCRIPTION

N-channel enhancement mode field-effect power transistor in a plastic full-pack envelope.
The device is intended for use in Switched Mode Power Supplies (SMPS), motor control, welding, DC/DC and AC/DC converters, and in general purpose switching applications.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
	BUK444	-500A	-500B	
V_{DS}	Drain-source voltage	500	500	V
I_D	Drain current (DC)	2.1	1.9	A
P_{tot}	Total power dissipation	25	25	W
$R_{DS(ON)}$	Drain-source on-state resistance	2.3	2.8	Ω

MECHANICAL DATA

Dimensions in mm

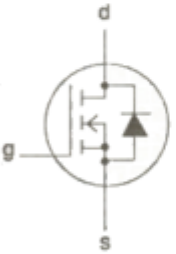
Net Mass: 2g

Pinning:

1 = Gate

2 = Drain

3 = Source



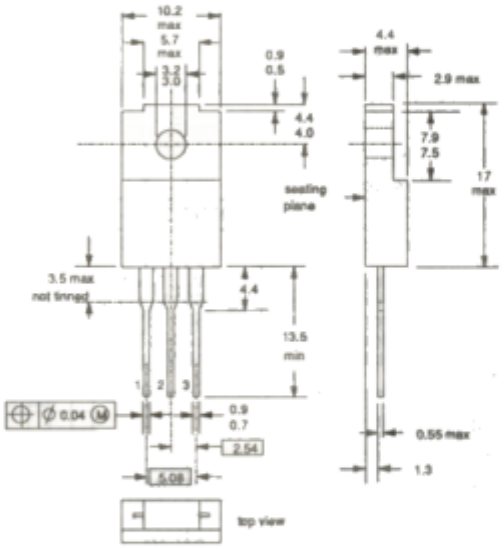


Fig.1 SOT-186; The seating plane is electrically isolated from all terminals.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Accessories supplied on request: refer to Mounting instructions for F-pack envelopes.

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PowerMOS transistor **BUK444-500A BUK444-500B**

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
V_{DS}	Drain-source voltage	-	-	500		V
V_{DGR}	Drain-gate voltage	R_{GS} = 20 kΩ	-	500		V
$\pm V_{GS}$	Gate-source voltage	-	-	30		V
				-500A	-500B	
I_D	Drain current (DC)	T_{hs} = 25 °C	-	2.1	1.9	A
I_D	Drain current (DC)	T_{hs} = 100 °C	-	1.3	1.2	A
I_{DM}	Drain current (pulse peak value)	T_{hs} = 25 °C	-	8.4	7.6	A
P_{tot}	Total power dissipation	T_{hs} = 25 °C	-	25		W
T_{stg}	Storage temperature	-	- 55	150		°C
T_j	Junction Temperature	-	-	150		°C

THERMAL RESISTANCES

From junction to heatsink	with heatsink compound	$R_{th\ j\text{-}hs}$ = 5 K/W
From junction to ambient		$R_{th\ j\text{-}a}$ = 55 K/W

STATIC CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.25 mA	500	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	V_{DS} = V_{GS}; I_D = 1 mA	2.1	3.0	4.0	V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 500 V; V_{GS} = 0 V; T_j = 25 °C	-	2	20	µA
I_{DSS}	Zero gate voltage drain current	V_{DS} = 500 V; V_{GS} = 0 V; T_j =125 °C	-	0.1	1.0	mA
I_{GSS}	Gate source leakage current	V_{GS} = ±30 V; V_{DS} = 0 V	-	10	100	nA
$R_{DS(ON)}$	Drain-source on-state resistance	V_{GS} = 10 V; I_D = 1.2 A; BUK444-500A	-	2.0	2.3	Ω
		BUK444-500B	-	2.4	2.8	Ω

DYNAMIC CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	V_{DS} = 25 V; I_D = 1.2 A	1.9	2.5	-	S
C_{iss}	Input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz	-	400	500	pF
C_{oss}	Output capacitance		-	55	80	pF
C_{rss}	Feedback capacitance		-	20	55	pF
$t_{d\ on}$	Turn-on delay time	V_{DD} = 30 V; I_D = 2.3 A;	-	15	20	ns
t_r	Turn-on rise time	V_{GS} = 10 V; R_{GS} = 50 Ω;	-	40	60	ns
$t_{d\ off}$	Turn-off delay time	R_{gen} = 50 Ω	-	50	65	ns
t_f	Turn-off fall time		-	30	40	ns
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH

ISOLATION

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65% ; clean and dustfree	-	-	1500	V
C_{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	12	-	pF

REVERSE DIODE RATINGS AND CHARACTERISTICS

T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	2.1	A
I_{DRM}	Pulsed reverse drain current	-	-	-	8.4	A
V_{SD}	Diode forward voltage	I_F = 2.1 A ; V_{GS} = 0 V	-	1.0	1.3	V
t_{rr}	Reverse recovery time	I_F = 2.1 A; $-dI_F/dt$ = 100 A/µs;	-	270	-	ns
Q_{rr}	Reverse recovery charge	V_{GS} = 0 V; V_R = 100 V	-	2.0	-	µC

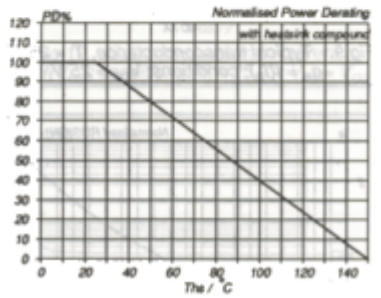

Fig.2. Normalised power dissipation.
$PD\% = 100 \cdot P_D/P_{D\,25\,°C} = f(T_{hs})$

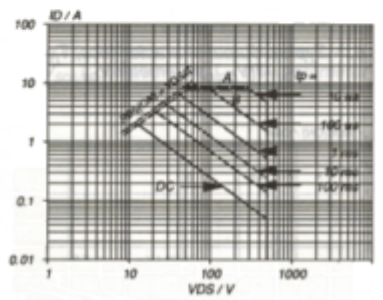

Fig.4. Safe operating area. T_{hs} = 25 °C
I_D & I_{DM} = $f(V_{DS})$; I_{DM} single pulse; parameter t_p

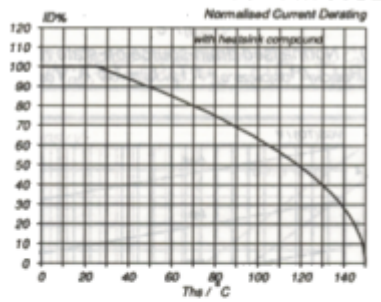

Fig.3. Normalised continuous drain current.
$ID\% = 100 \cdot I_D/I_{D\,25\,°C} = f(T_{hs})$; conditions: $V_{GS} \geq 10$ V

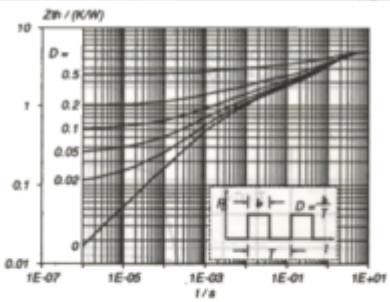

Fig.5. Transient thermal impedance.
$Z_{th\,j\text{-}hs} = f(t)$; parameter $D = t_p/T$

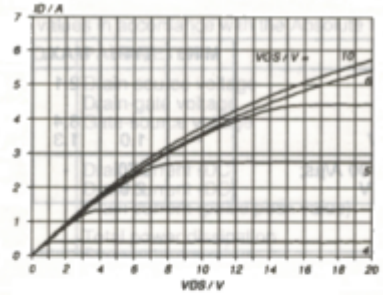

Fig.6.[1] *Typical output characteristics, T_j = 25 °C. $I_D = f(V_{DS})$; parameter V_{GS}*

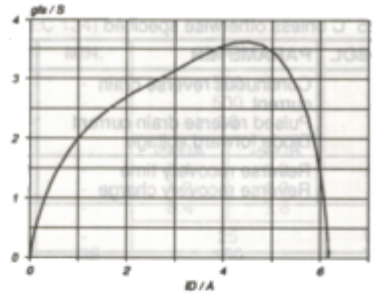

Fig.9. Typical transconductance, T_j = 25 °C. $g_{fs} = f(I_D)$; conditions: V_{DS} = 25 V

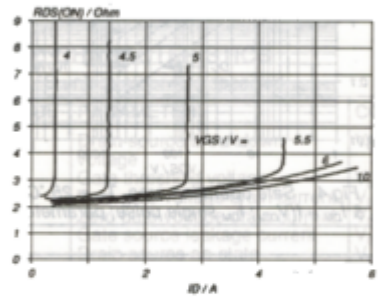

Fig.7. Typical on-state resistance, T_j = 25 °C. $R_{DS(ON)} = f(I_D)$; parameter V_{GS}

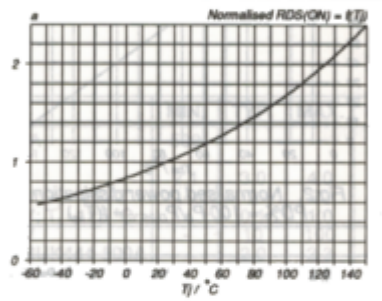

Fig.10. Normalised drain-source on-state resistance. $a = R_{DS(ON)}/R_{DS(ON)25\,°C} = f(T_j)$; I_D = 1.5 A; V_{GS} = 10 V

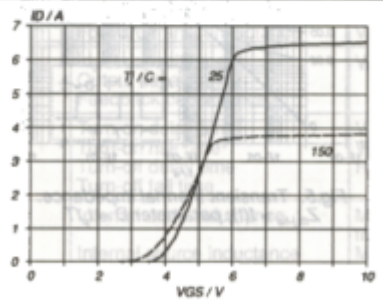

Fig.8. Typical transfer characteristics. $I_D = f(V_{GS})$; conditions: V_{DS} = 25 V; parameter T_j

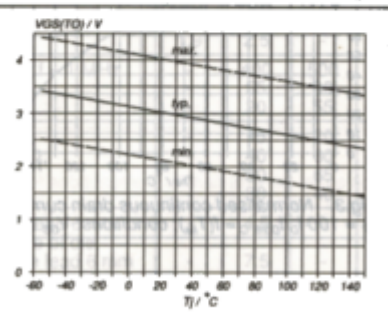

Fig.11. Gate threshold voltage. $V_{GS(TO)} = f(T_j)$; conditions: I_D = 1 mA; $V_{DS} = V_{GS}$

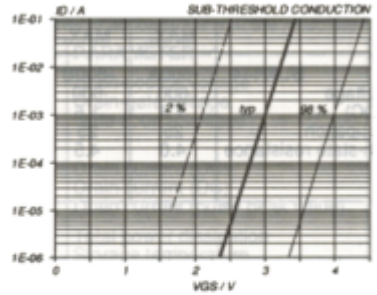

Fig.12. Sub-threshold drain current.
$I_D = f(V_{GS})$; conditions: $T_j = 25$ °C; $V_{DS} = V_{GS}$

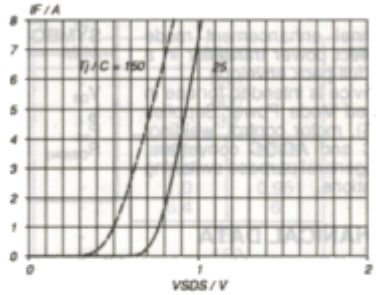

Fig.15. Typical reverse diode current.
$I_F = f(V_{SDS})$; conditions: $V_{GS} = 0$ V; parameter T_j

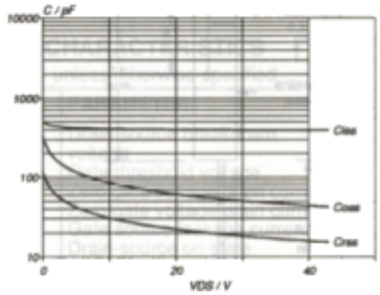

Fig.13. Typical capacitances, C_{iss}, C_{oss}, C_{rss}.
$C = f(V_{DS})$; conditions: $V_{GS} = 0$ V; f = 1 MHz

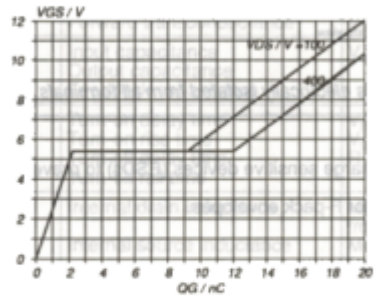

Fig.14. Typical turn-on gate-charge characteristics.
$V_{GS} = f(Q_G)$; conditions: $I_D = 3.7$ A; parameter V_{DS}